Electronic Supplementary Material (ESI) for Physical Chemistry Chemical Physics.

Type-II Tunable SiC/InSe Heterostructure in Electric Field and Biaxial Strain

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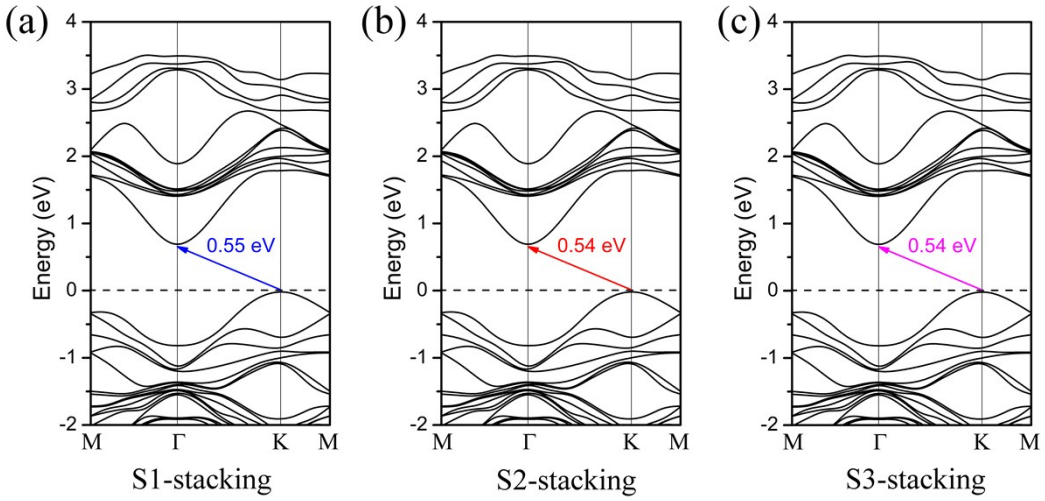

Fig. S1. Projected band structure of S1-stacking (a), S2- stacking (b) and S3- stacking (c).

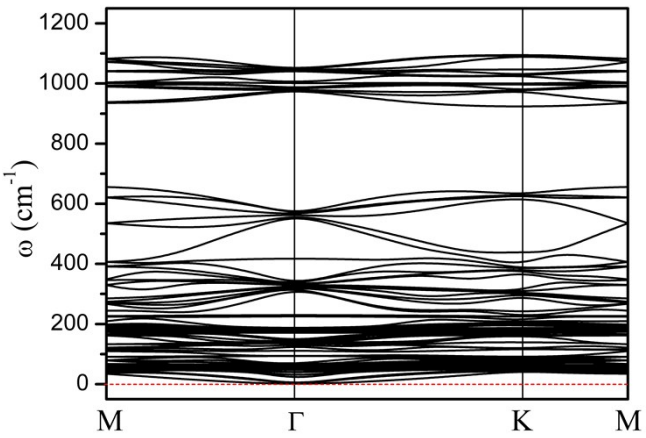

Fig. S2. The phonon dispersion of SiC/InSe heterostructure (d = 3.34 Å).

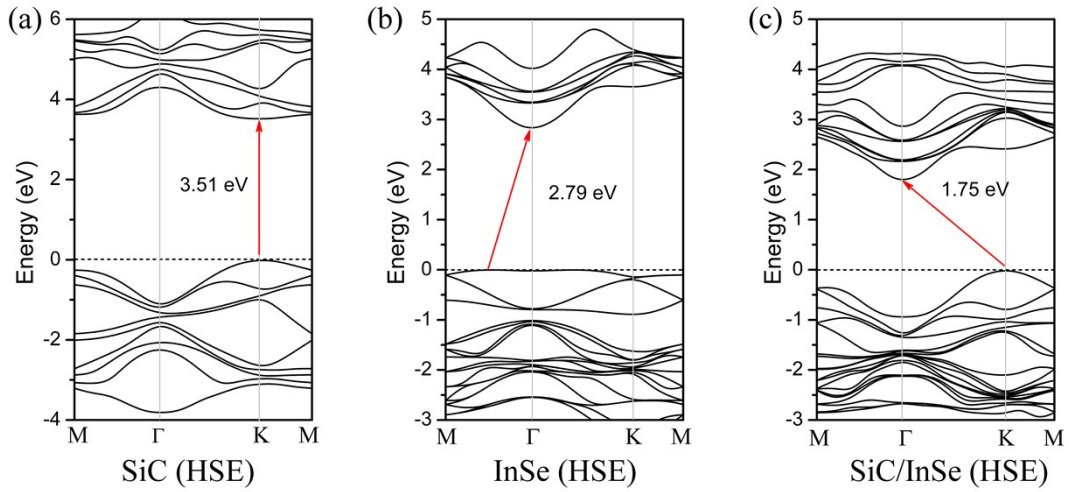

Fig. S3. (a)-(c) Projected energy band structures of the freestanding SiC, InSe monolayer, and the SiC/InSe heterostructure calculated by HSE06.

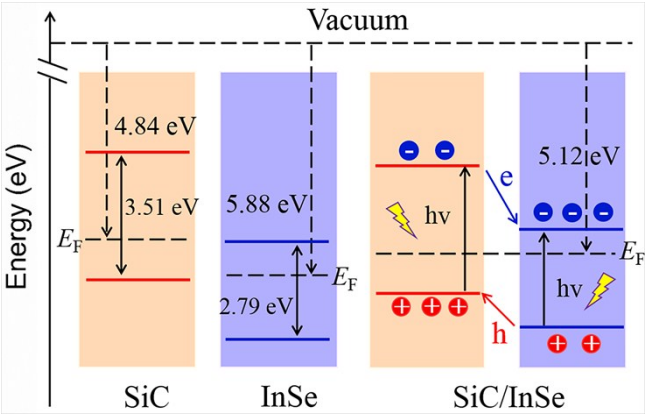

Fig. S4. Band alignment (HSE06) of the SiC, InSe single layers, and SiC/InSe

heterostructure, with the vacuum level being used as a reference.